JST16A-800C 16A TRIAC

Rev.A.1.2

DESCRIPTION:

The JST16A-800C

Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33Ω	- -	MAX.	25	mA
				50	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	40	mA
				80	
I_H	I_T=500mA		MAX.	40	mA
dV/dt	V_D=540V Gate Open T_j=125		MIN.	500	V/μs
(dV/dt)c	(dI/dt)c=7A/ms, T_j=125		MIN.	6	V/μs
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V_{TM}	I_{TM}=22.5A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	30	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

J ST 16 A -800 C

JieJie Microelectronics Co., Ltd.

Triacs

800:V_{DRM} /V

RMS on-state current versus case
rature